

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings of claims in the application:

#### **Listing of Claims:**

Claims 1-2 (Canceled)

Claim 3 (Currently Amended): The method according to claim 21 [[1]], wherein the predetermined temperature is a temperature of from 200°C to 400°C.

Claim 4 (Currently Amended): The method according to claim 21 [[1]], wherein the metallic layer is formed on the ~~amorphous~~ silicon region by a long throw sputtering method or a collimate sputtering method.

Claim 5 (Currently Amended): The method according to claim 21 [[1]], wherein the metallic layer is comprised of titanium, cobalt or nickel.

Claim 6 (Currently Amended): The method according to claim 21 [[1]], wherein a depth of the silicon region is larger than the first thickness of the metallic layer.

Claim 7 (Currently Amended): The method according to claim 21 [[1]], wherein the

protective layer is comprised of titanium-nitride or tungsten.

Claim 8 (Currently Amended): The method according to claim 21 ~~[[1]]~~, wherein the first thickness of the metallic layer is equal to or less than 15nm.

Claim 9 (Currently Amended): The method according to claim 21 ~~[[1]]~~, wherein the second thickness of the protective layer is equal to or more than 30nm.

Claim 10 (Currently Amended): The method according to claim 21 ~~[[1]]~~, wherein a source region and a drain region of ~~[[a]]~~ an MOS transistor are formed in the silicon region, wherein the metallic silicide layer is formed in the source and drain regions.

Claims 11-20 (Canceled)

Claim 21 (New): A method for fabricating a semiconductor device, comprising:

preparing a substrate having a silicon region;

heating the substrate at a predetermined temperature;

forming a metallic layer on the silicon region of the heated substrate by a straight sputtering method so as to sputter straightly to the silicon region, wherein the metallic layer has a first thickness;

forming a protective layer on the metallic layer, wherein the protective layer

protects the metallic layer from a surrounding atmosphere and wherein the protective layer has a second thickness greater than the first thickness; and

forming a metallic silicide layer in an interface between the silicon region and the metallic layer by a heat treatment, after said forming a protective layer,

wherein the metallic silicide layer is comprised of metal from the metallic layer and silicon from the silicon region.

Claim 22 (New): The method according to claim 10, wherein the MOS transistor also includes a polysilicon gate, said forming a metallic layer comprises forming the metallic layer on the gate, and

Wherein the metallic silicide layer is formed in an interface between the polysilicon gate and the metallic layer.